

ABSTRACT OF THE DISCLOSURE

5 Thin-layer electronic device, in particular a thin-layer power device, and process for fabricating this device.

 According to the invention, an electronic device is formed comprising an active part (38,40,42), a first thin layer (36) which is made of a semiconductor material and in
10 which this active part is formed, and a substrate (44) which is made of a conductive material. This device also comprises a carrier recombination zone(46) which is located between the substrate and the first thin layer and which also ensures a resistive electric contact between this substrate and this
15 first thin layer.

 Figures 5A to 5D.